



## (一)新機介紹: 超高解析冷槍場放射型掃描式電子顯微鏡(主機) 含 TE detector 及空氣阻斷系統

型號: UHR CFE-SEM (SU8220-TE detecting device)

功能簡介: 電壓範圍 0.01KV~30KV ; 解析度高(15KV 達 0.8nm ; 1KV 達

1.1nm ; 放大倍率最高達 1,000,000X ; 樣品移動為五軸全自動式;備有減速電壓

(Landing voltage)降低電子束對樣品的破壞;同時具有

頂部、上、下 三組二次電子偵測器與背向電子訊號偵測器並搭載穿透電子偵測

裝置 TE Detecting Device (Aperture For Bright/Dark Field STEM / STEM

Holder)可以同時同地觀測 SEM+TEM-BF+TEM-DF 影像。另外具有可與離子切

割研磨機(HITACHI IM4000+)相容之空氣阻斷系統(Air protection unit)可達樣品

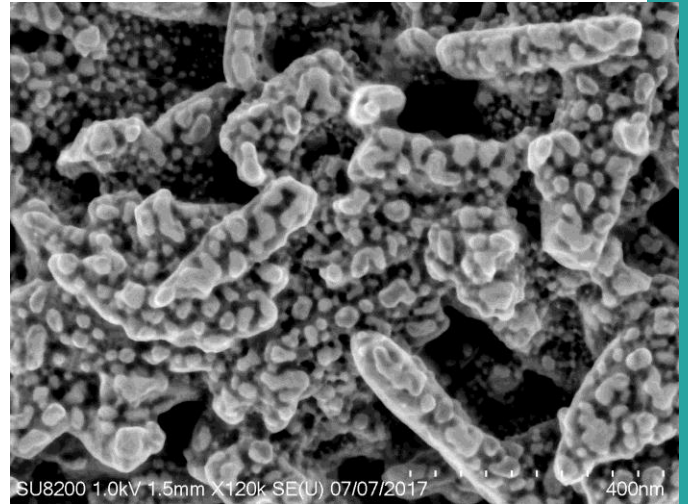
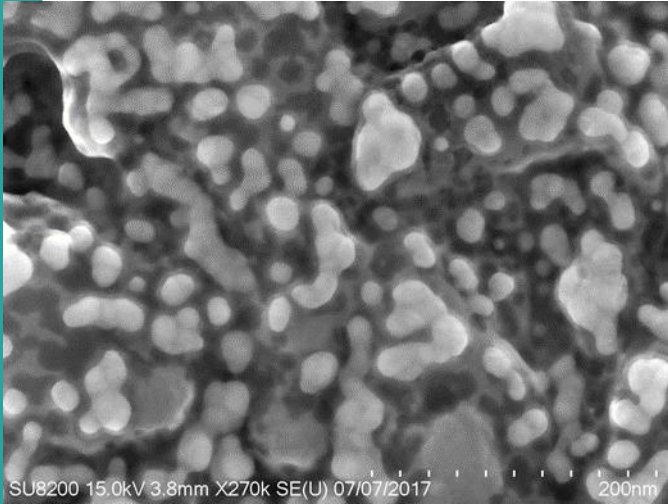
由製作-切割-觀測分析皆處於真空狀態。



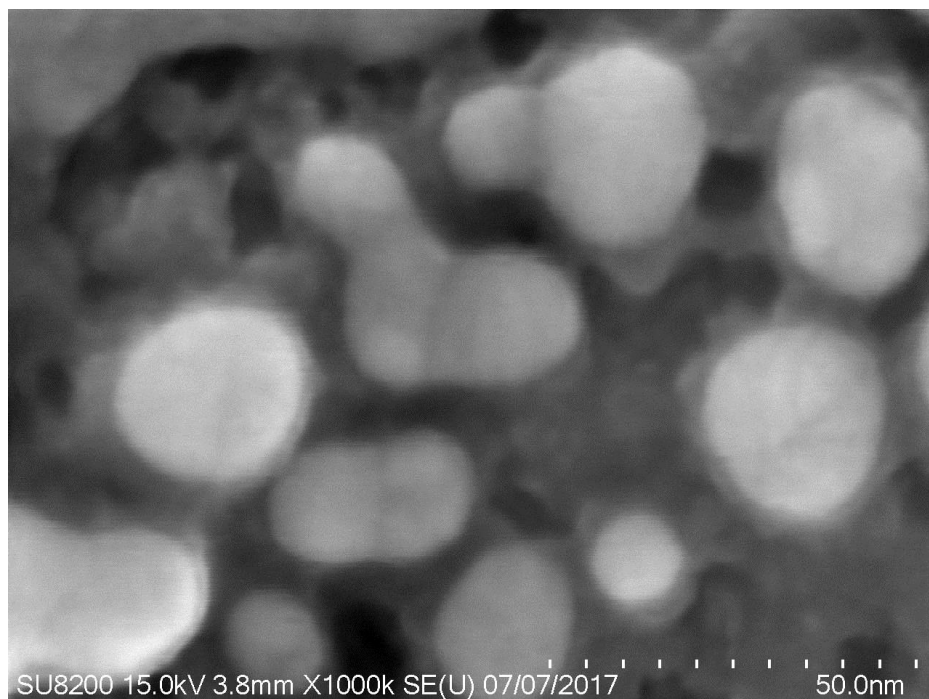
樣品實測:

(1) UHR CFE-SEM (SU8220) 部份 (UN-COATING)

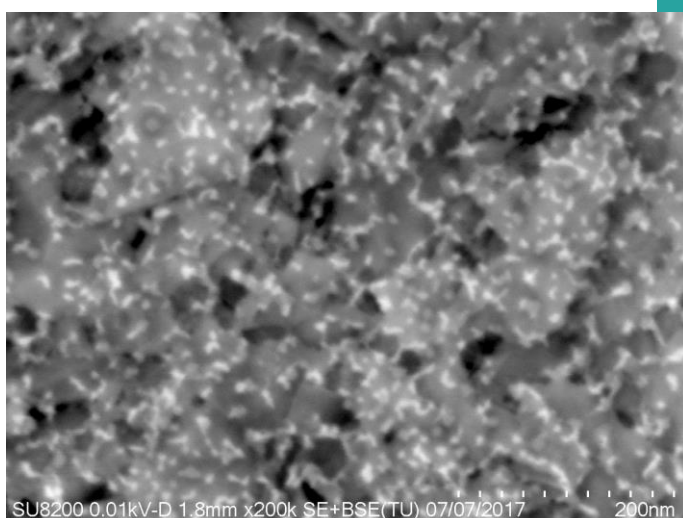
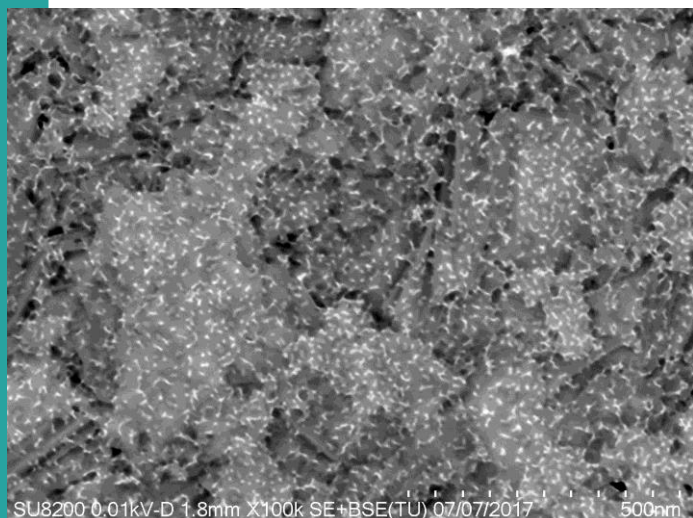
A. 標準的 SU8220 驗機解析度影像



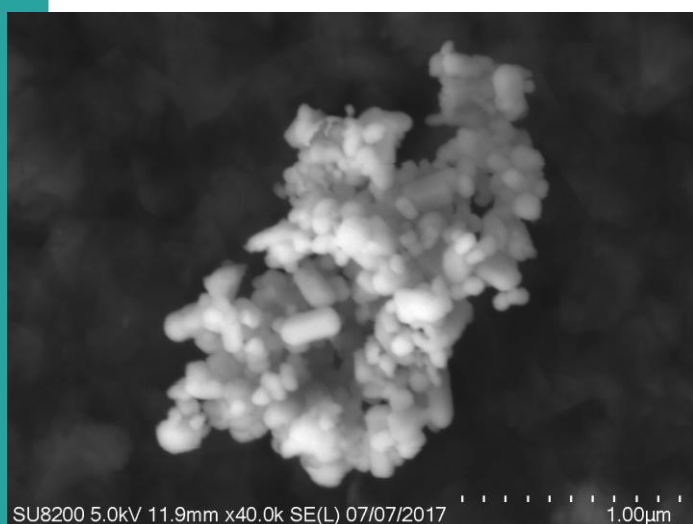
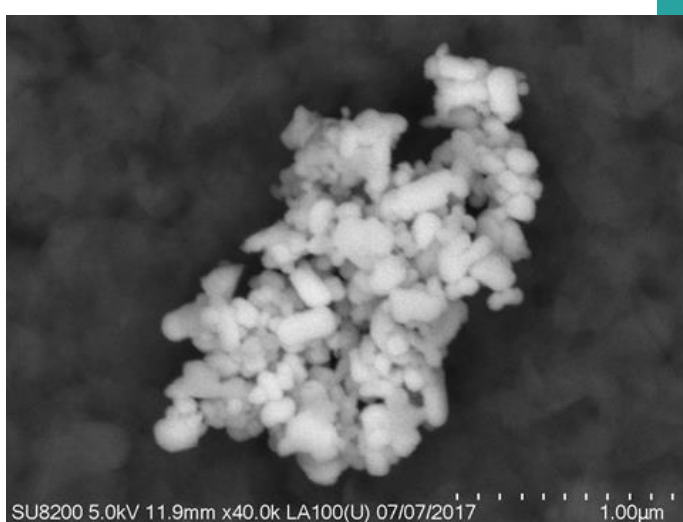
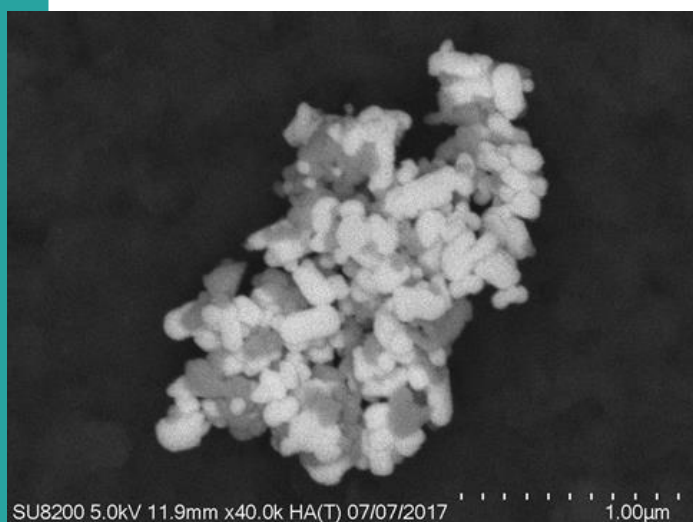
B. SU8220 最高放大倍率影像 (1000K)



### C. SU8220 減速電壓影像 (最低加速電壓為 10V)

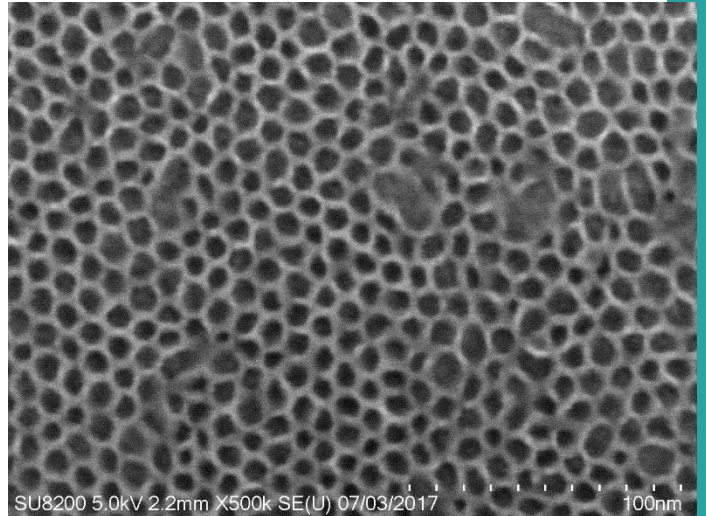


### D. SU8220 三組二次電子偵測器 (TOP、UPPER 和 LOWER)

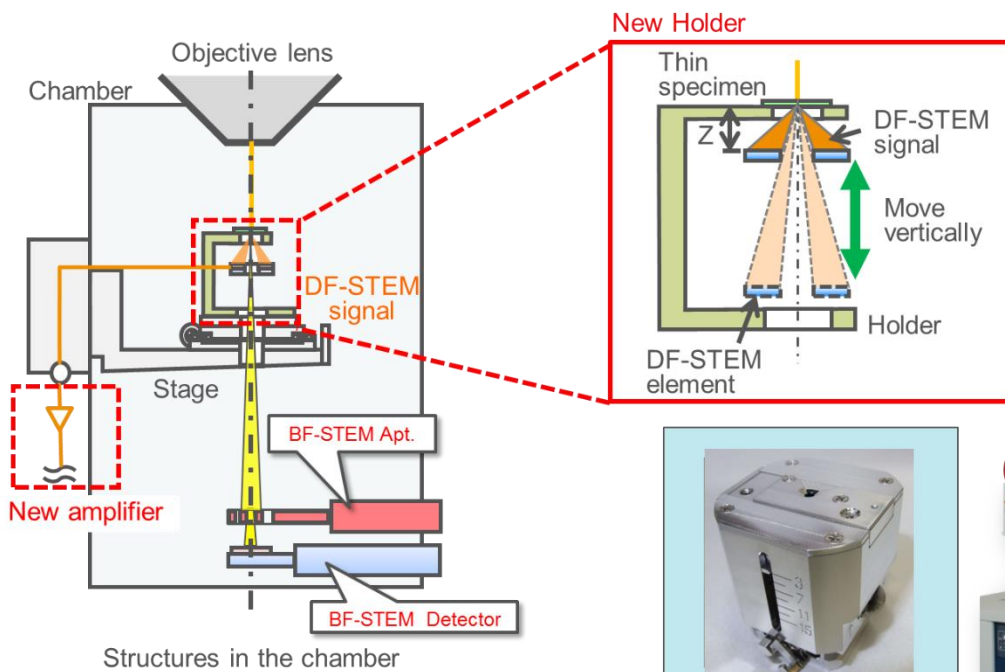


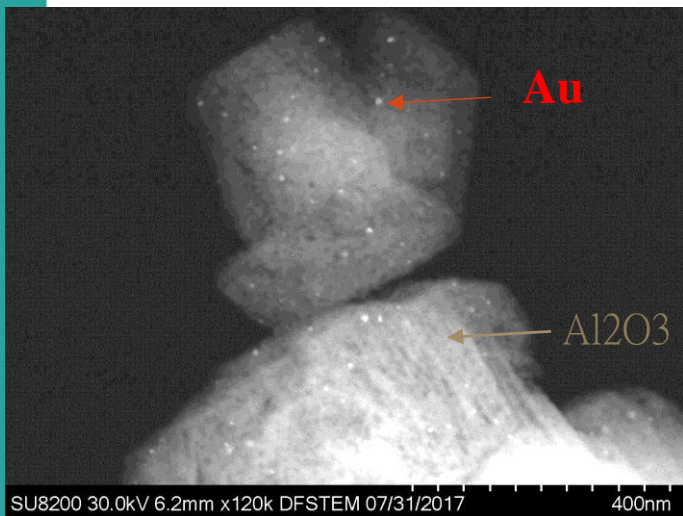
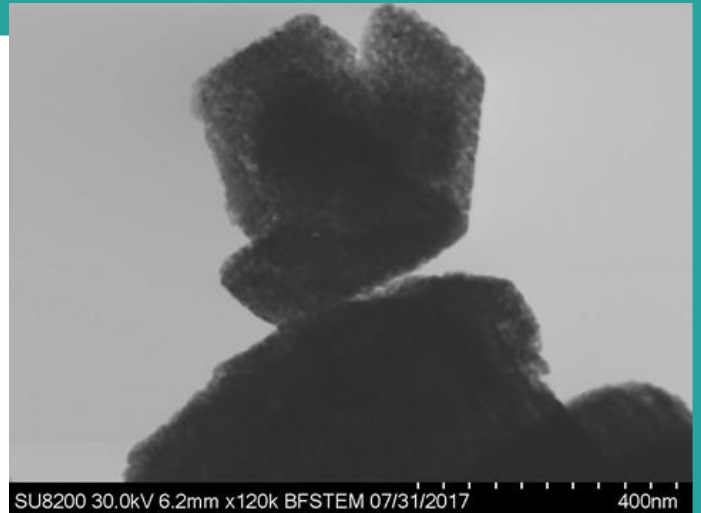
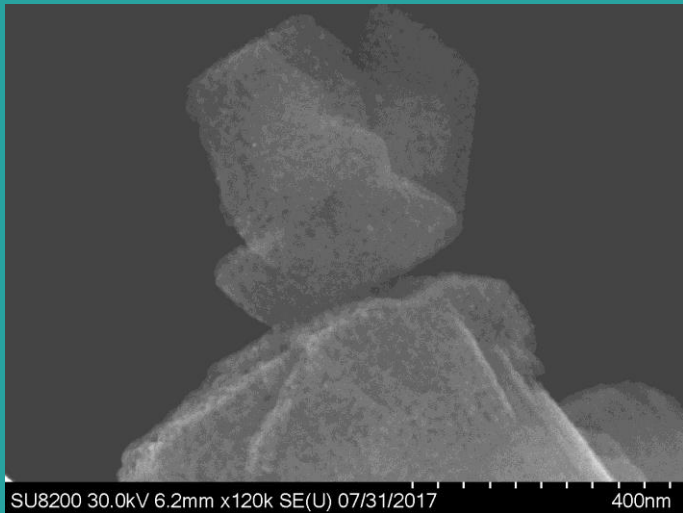
TOP 偵測器觀察的影像  
其組成相對比較明顯;  
LOWER 偵測器觀察的  
SE(L)影像, 其為 3D 立  
體影像。

## E. SU8220 超微孔影像

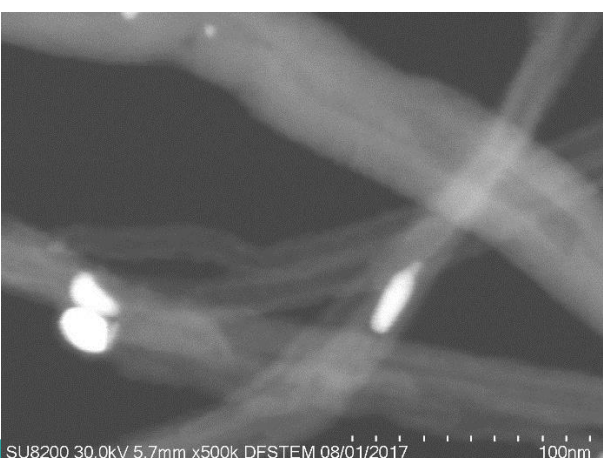
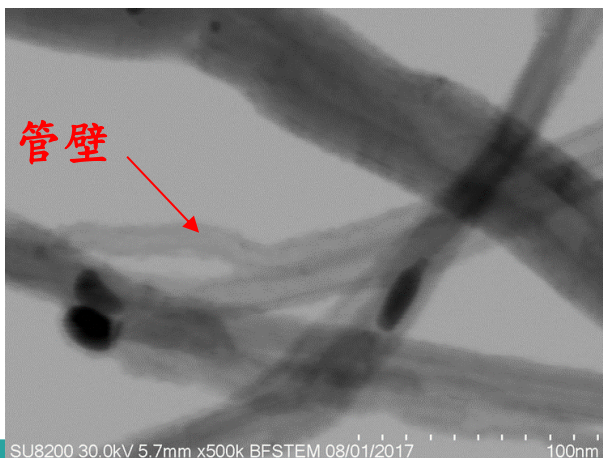
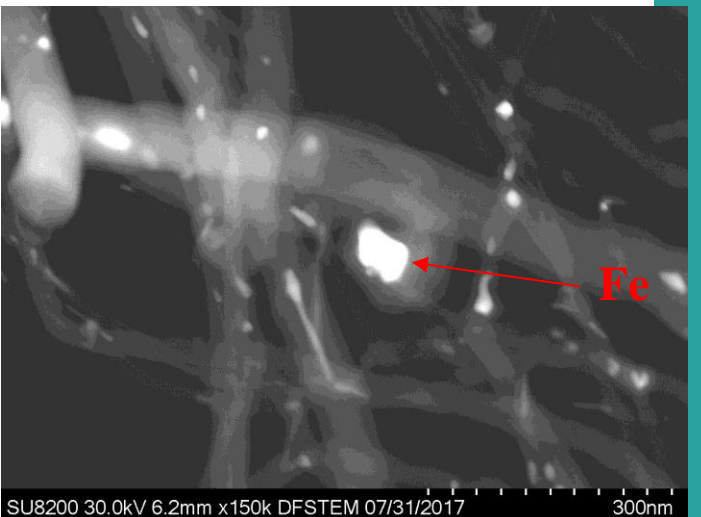
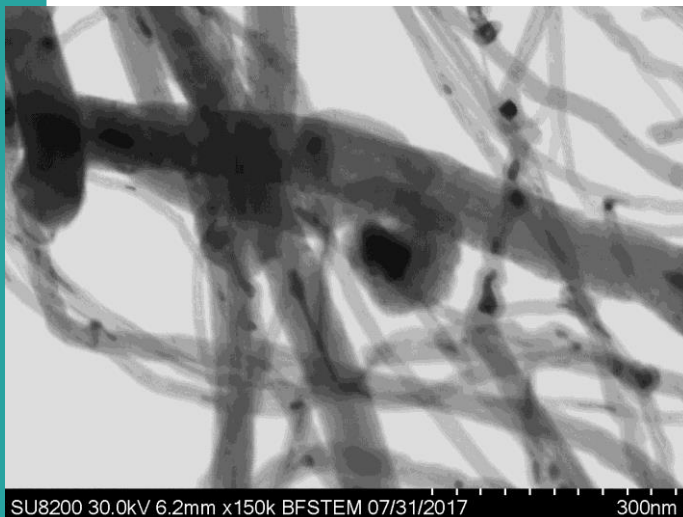


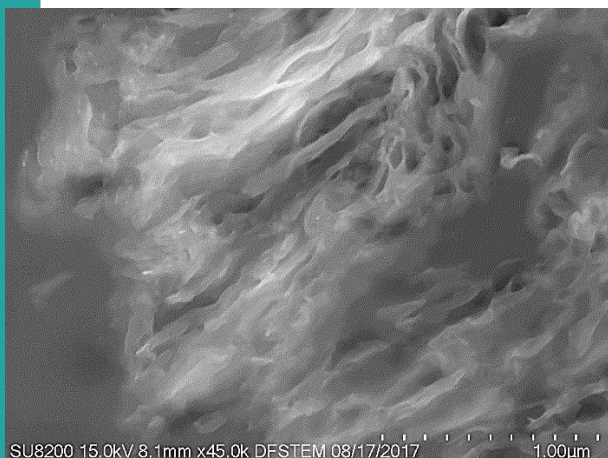
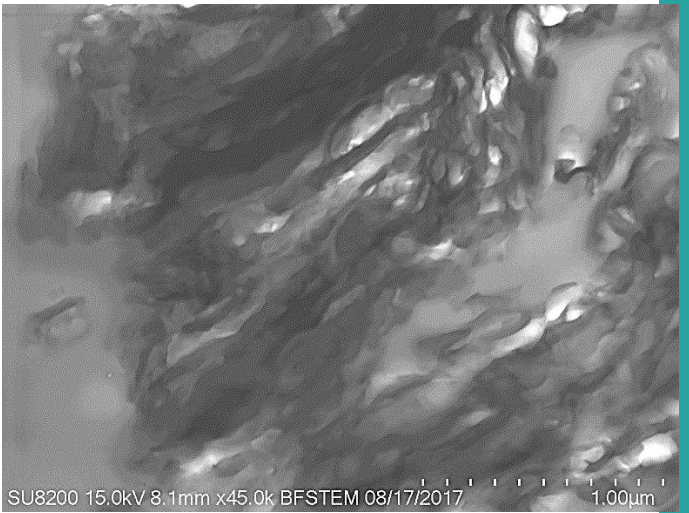
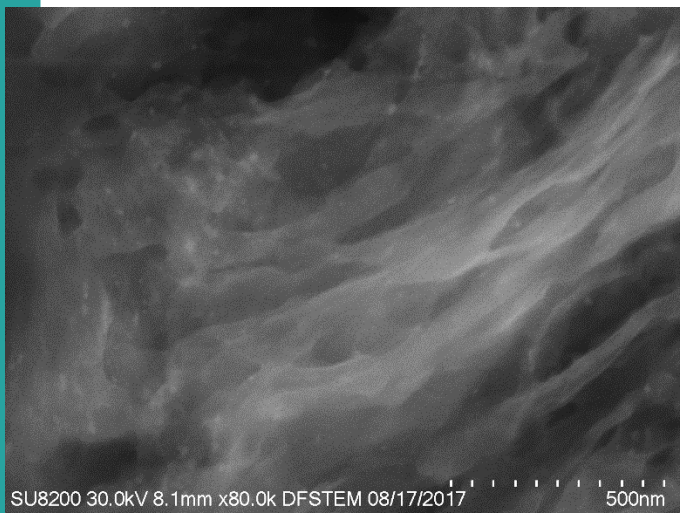
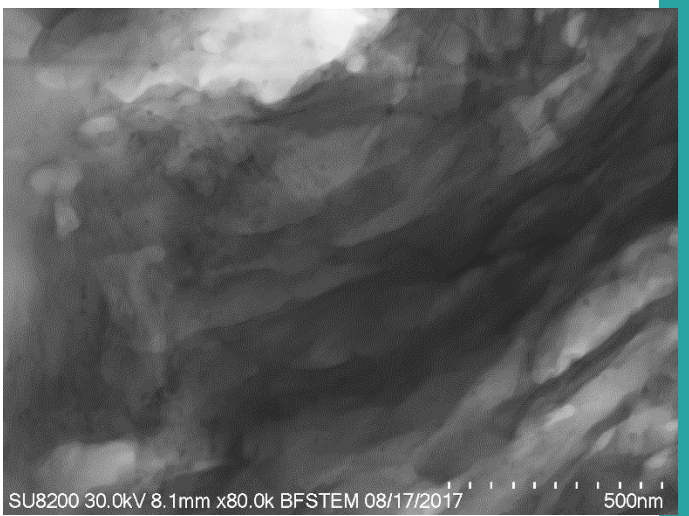
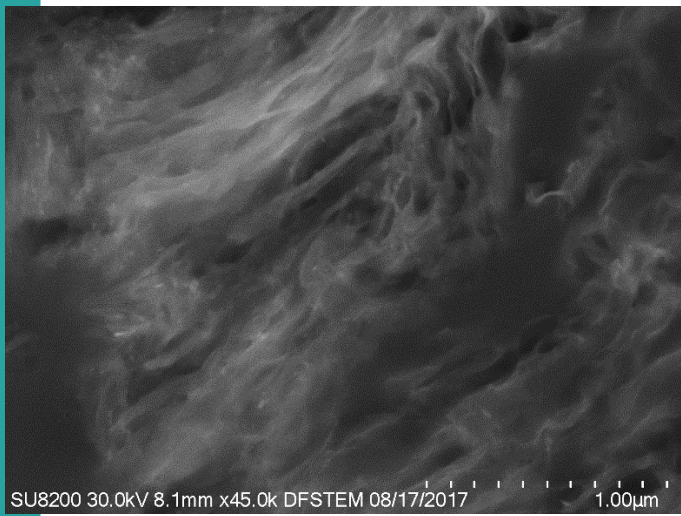
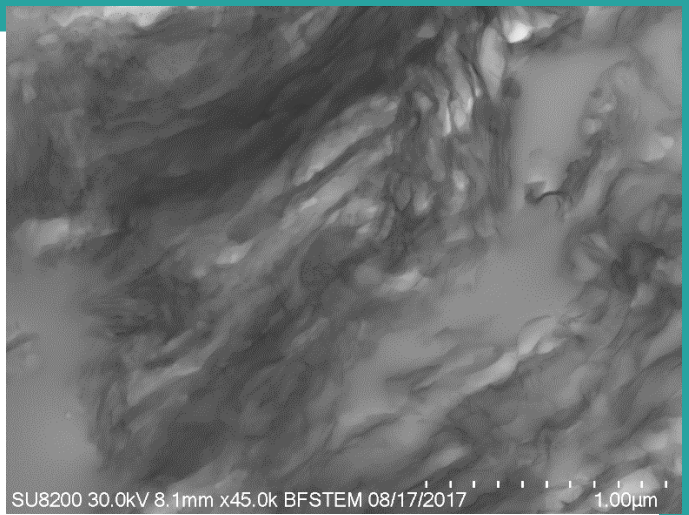
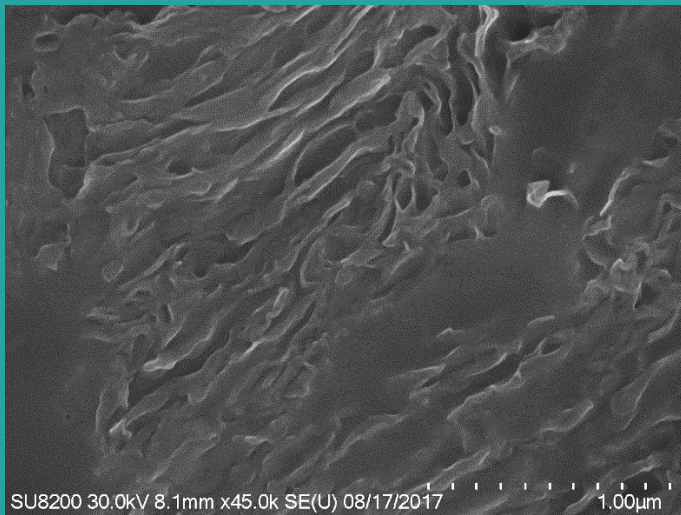
## F. SU8220 STEM 影像(同時同地觀測 SEM+TEM-BF+TEM-DF)



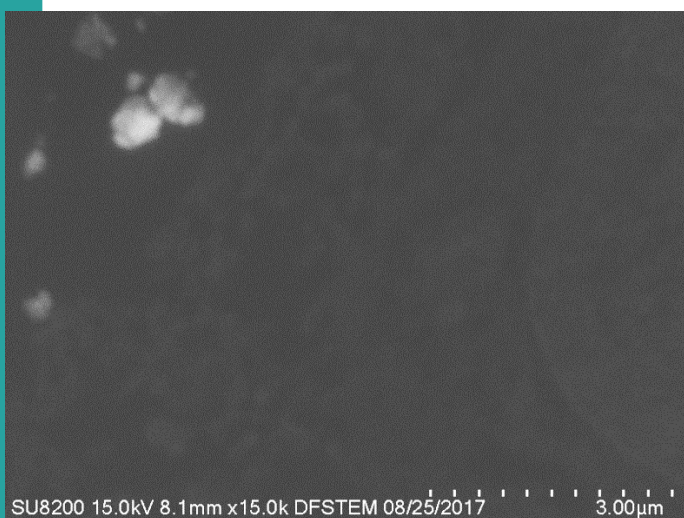
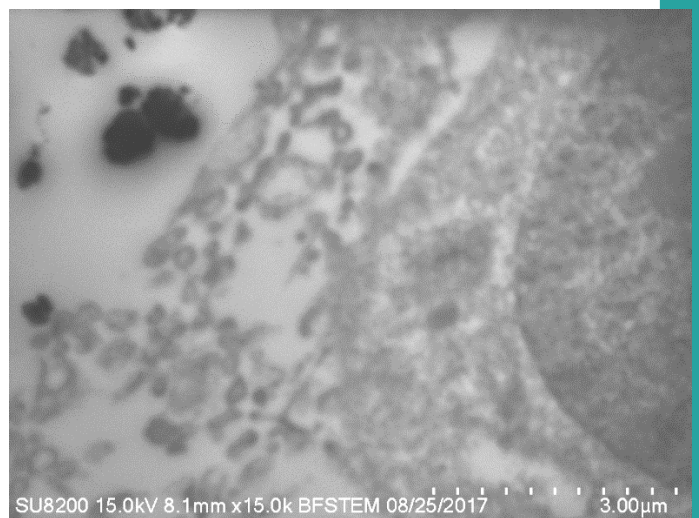
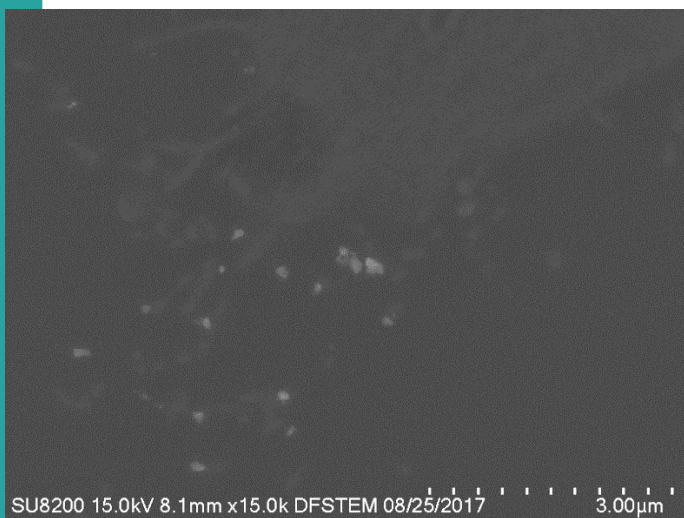
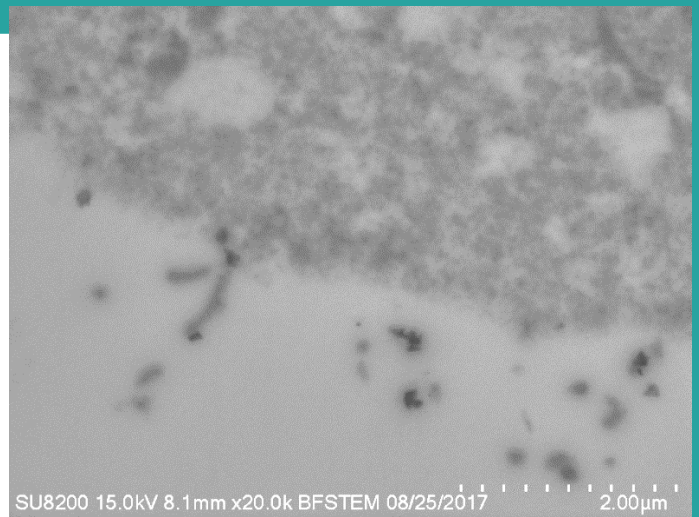
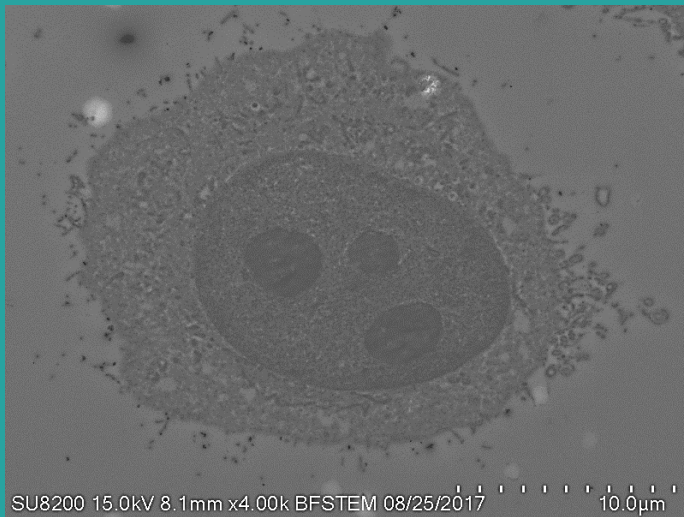


TEM 粉末樣品，製備於  
一般鍍碳銅網上直接進  
SU8220 TE DETECTING  
DEVICE。

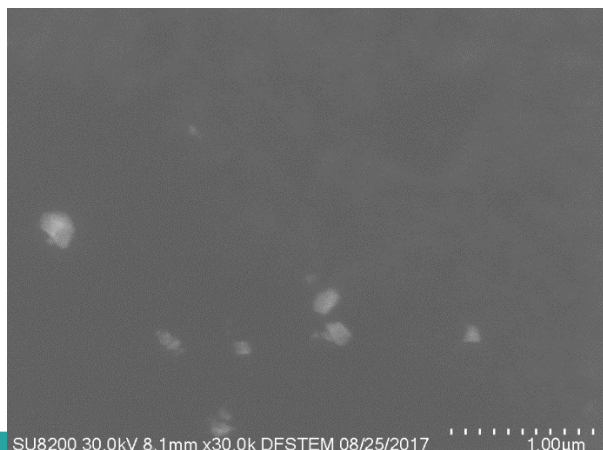
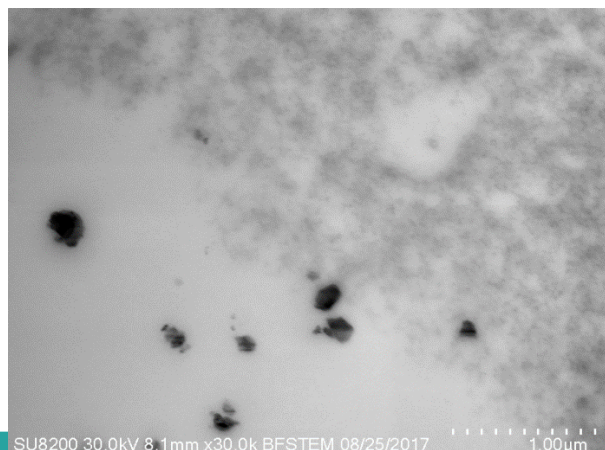




高分子樹脂內含 GO 之 TEM 超薄切片  
樣品，製備於一般鍍碳銅網上直接進  
SU8220 TE detecting device; 使用  
15KV 亦可穿透並觀測。



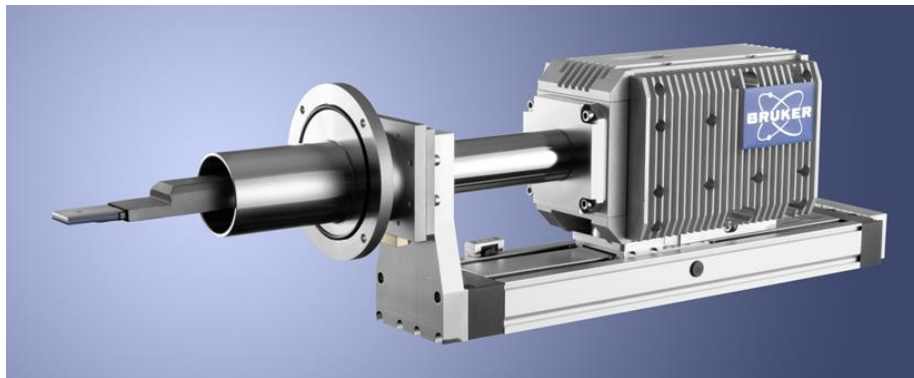
結晶奈米顆粒與纖維狀細胞間作用情況之 TEM 未染色超薄切片 樣品，製備於一般鍍碳銅網上直接進 SU8220 TE detecting device; 使用 15KV 亦可穿透並觀測。



## (二)新機介紹: X 光能量分散光譜儀

型號: QUANTAX ANNULAR XFLASH® QUAD FQ5060

功能簡介:微區顯微成分之定性及半定量分析(Spectrum Quantification)、多點分析(Objection Quantification), 線分析(Line Scan) 及面元素分佈分析 (Mapping)

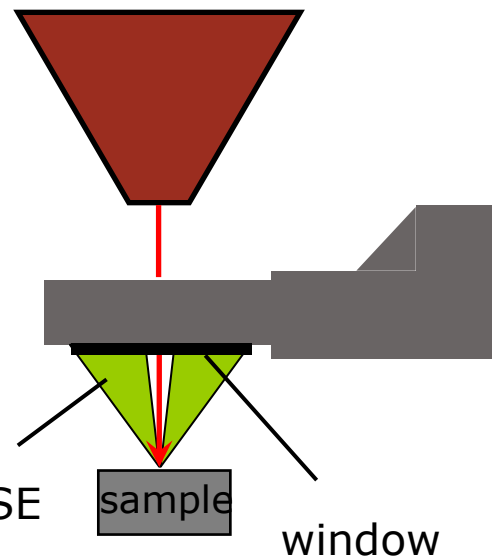
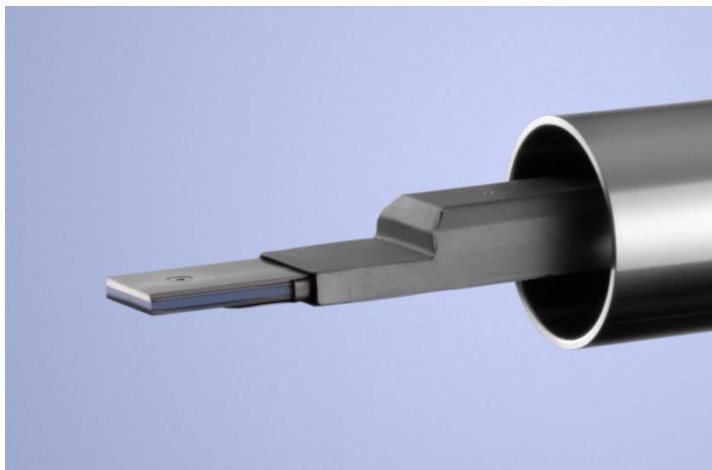
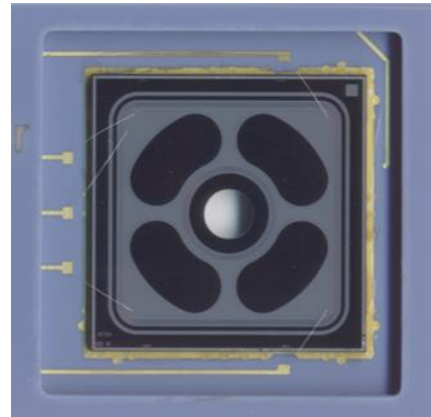
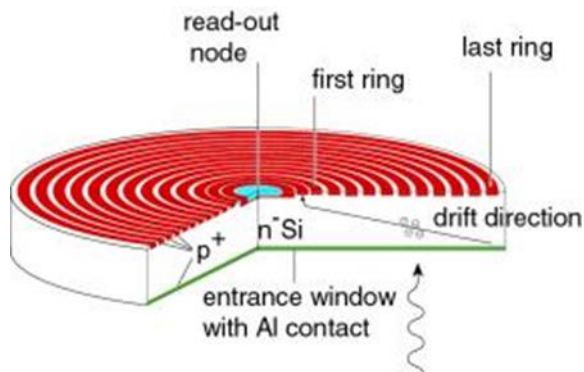


### 儀器規格

- ◆ **Active area(訊號接收面積) : 60 mm<sup>2</sup> (4 x 15 mm<sup>2</sup>)**
- ◆ **Detection element(偵測元素範圍) : Boron (z=5) to Americium (z=95)**
- ◆ **Energy resolution(能量解析度) : ≤124 eV (MnK  $\alpha$  , 100 000 cps)**
- ◆ **Maximum input count rate(最大訊號接收量) : > 2 million cps**
- ◆ **Cooling(冷卻方式) : Peltier cooled**
- ◆ **Quantification Software 定量軟體—ESPRIT 2.0 版**
- ◆ **Objection, Line Scan and Mapping 多點/區分析, 線分析及面元素分佈分析**



## 偵測器種類: Silicon Drift Detectors



X-rays+BSE

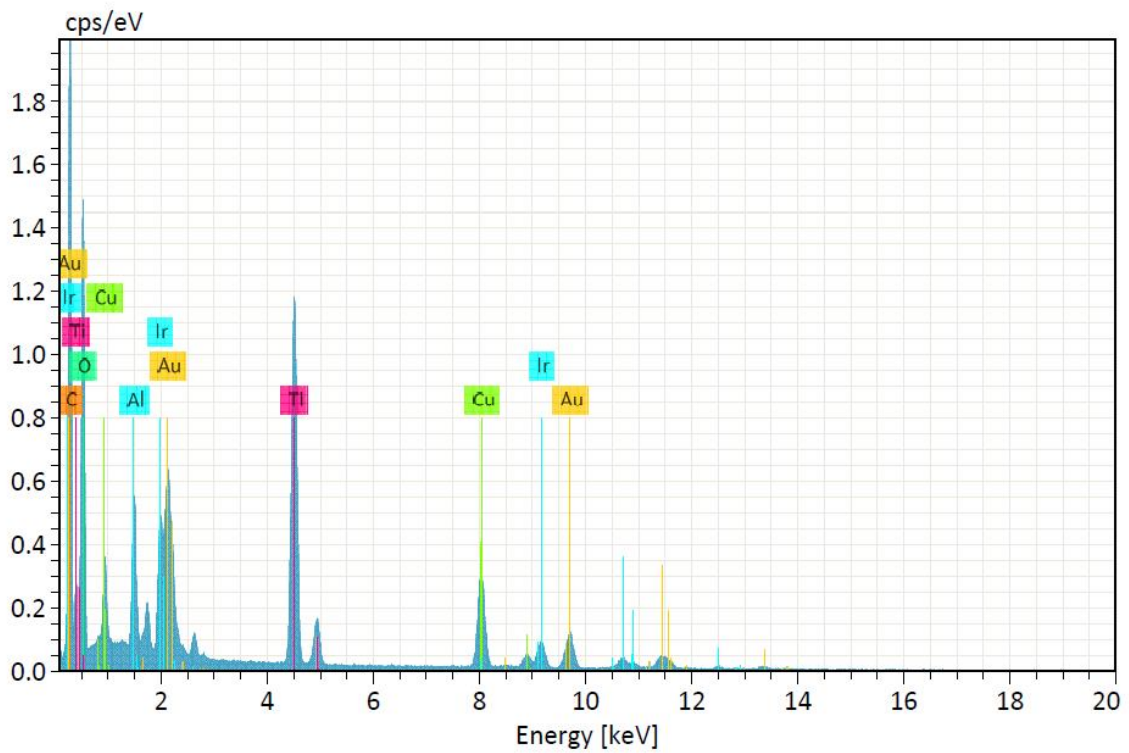
window

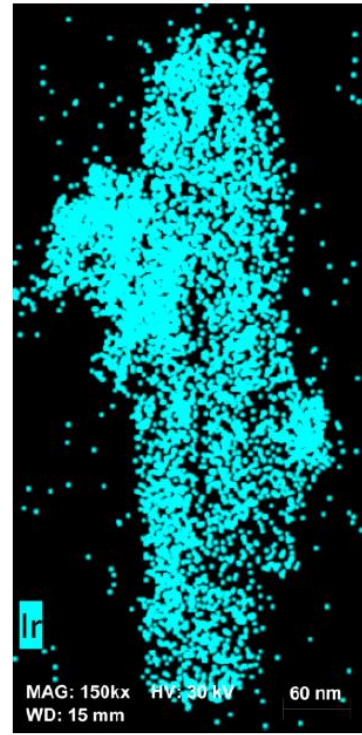
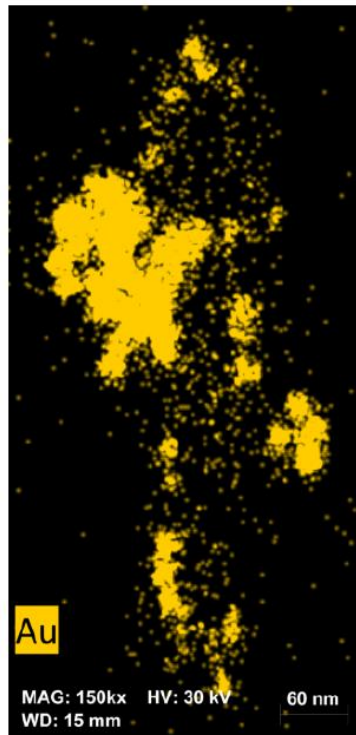
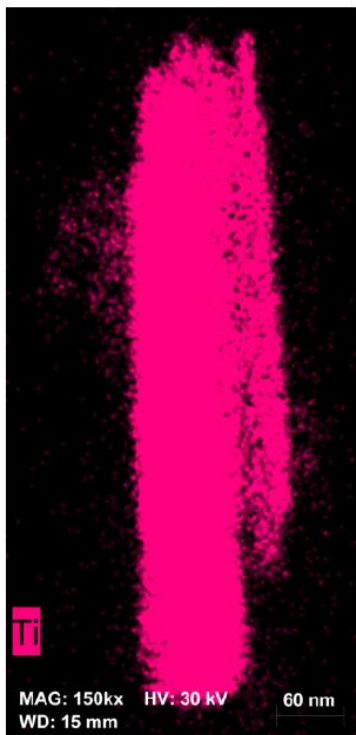
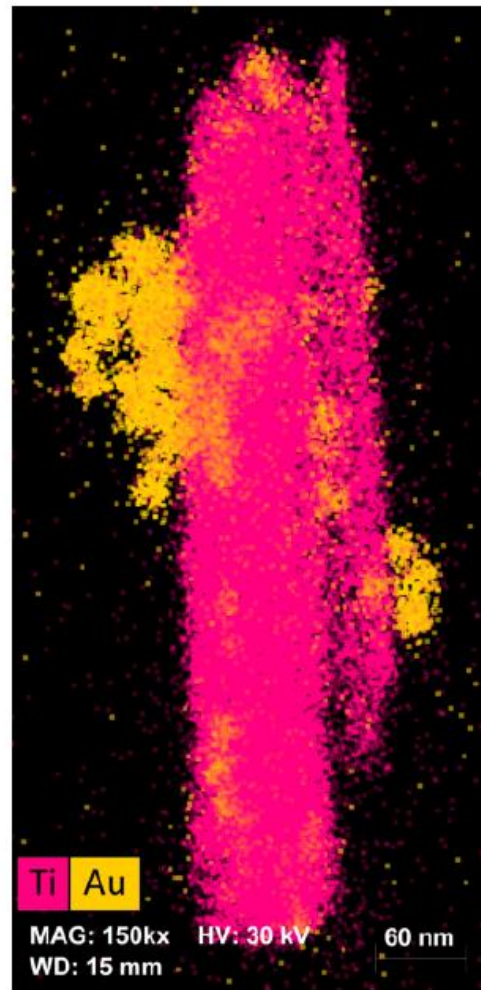
- Detector is equipped with a polymer window
- Influence of BSE needs special treatment in this geometry
- Electron trap cannot be used
- Depending on acceleration voltage BSE can affect the quality of the spectrum
- Thick polymer or Be window will block high energy BSE, e.g. HV=20kV, but will reduce low energy X-ray detection
- Thin polymer window: will enhance low energy efficiency but will only block BSE up to a certain HV

# 様品試作分析

## Application Note

Company / Department





### (三) 新機介紹：離子切割研磨機含冷凍控溫及空氣阻斷系統 (Ion Milling with Cooling control unit and Air Protection System)

型號: IM4000 Plus

功能簡介:同時具有切割與研磨功能，利用氬氣來進行切割並結合液態氮控溫系統(控溫範圍:0~-100°C)。本設備同時具有空氣阻斷系統可以與 UHR CFE-SEM (SU8220-TE detecting device)相容，達到樣品由製作-切割-觀測分析皆處於真空狀態。

#### 儀器規格

- (1) Ion Gun 離子槍
  - a) Gas 氣體：Argon gas 氬氣
  - b) Acceleration Voltage 加速電壓：0 to 6kV
- (2) Cross-section polish 離子切割模式
  - a)切割速率： $>500\mu\text{m/hr}$ .
  - b)試片尺寸：最大尺寸 20W x 12D x 7H (mm)
- (3) Flat milling 離子研磨模式
  - a)研磨速率： $>20\mu\text{m/hr}$
  - b)試片尺寸：最大尺寸  $\Phi 50$  x 25H (mm)
- (4) Cooling Temperature control unit 溫控系統
  - a)冷卻源：LN2
  - b)控溫範圍：0 to 100°C
- (5) Alignment System 對位系統：配備高解析數位變倍顯微鏡對位系統



## (四) 新機介紹: 桌上型 SEM 試片清潔機( DESKTOP SEM SAMPLE CLEANER)

型號: Hitachi Zone SEM

功能簡介: 屬於軟性材料清潔保護設備 (UV CLEANER), 為非破壞性清潔方法, 主要針對目標表面的碳氫化合物污染以達到顯露精細表面特徵, 降低並消除了 ELECTRON BEAM INDUCED DEPOSITION (EBID) 現象, 進而提高成像和分析品質。

### 儀器原理

